

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	3.3mΩ@10V	170A

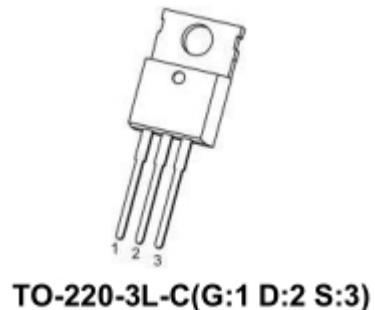
Feature

- Fast Switching
- Low Gate Charge and Rdson
- 100% Single Pulse avalanche energy Test

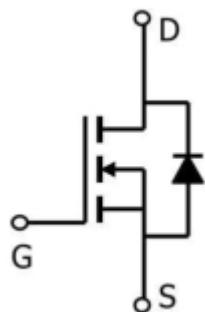
Application

- Power switching application DC-DC Converter
- Power Management

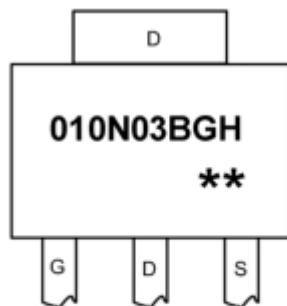
Package



Circuit diagram



Marking



010N03BGH : Product code
****** : Week code

Absolute maximum ratings

($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_c = 25^\circ\text{C}$)	I_D	170	A
Pulsed Drain Current	I_{DM}	680	A
Power dissipation($T_c=25^\circ\text{C}$)	P_D	250	W
Single Pulse Avalanche Energy ¹	E_{AS}	180	mJ
Thermal Resistance Junction-Case	$R_{\theta JC}$	0.5	$^\circ\text{C}/\text{W}$
Operation and storage temperature	T_{STG}, T_J	-55~ +150	$^\circ\text{C}$



ZL MOSFET

ZL010N03BGHB

Electrical characteristics

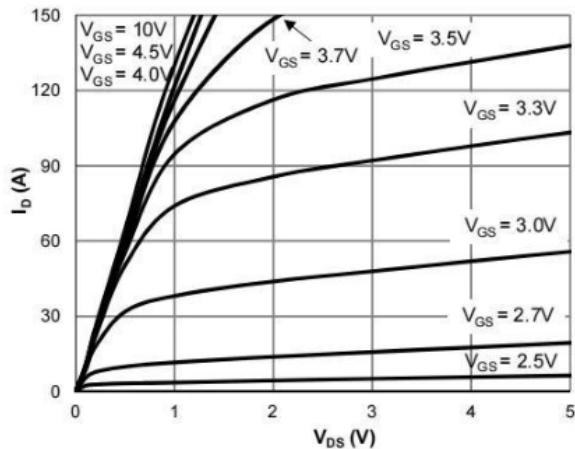
(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Drain Cut-Off Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V			1	uA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±0.1	uA
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	2.7	4	V
Drain-Source on-Resistance	R _{DS(on)}	V _{GS} = 10V, I _D = 30A		3.3	4.2	Ω
Dynamic characteristics						
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, f=1MHz		4660		pF
Output Capacitance	C _{oss}			1208		
Reverse Transfer Capacitance	C _{rss}			28		
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} =50V, V _{GS} =10V, I _D =20A		79		nC
Gate-Source Charge	Q _{gs}			12		
Gate-Drain Charge	Q _{gd}			25		
Turn-On Delay Time	T _{d(on)}	V _{GS} =10V, V _{DS} =50V, R _L =2.5Ω, R _G =6.0Ω		12		nS
Rise Time	T _r			23		
Turn-Off Delay Time	T _{d(off)}			85		
Fall Time	T _f			62		
Diode Characteristics						
Diode Forward Voltage2	V _{SD}	V _{GS} =0V, I _S =1A			1.2	V

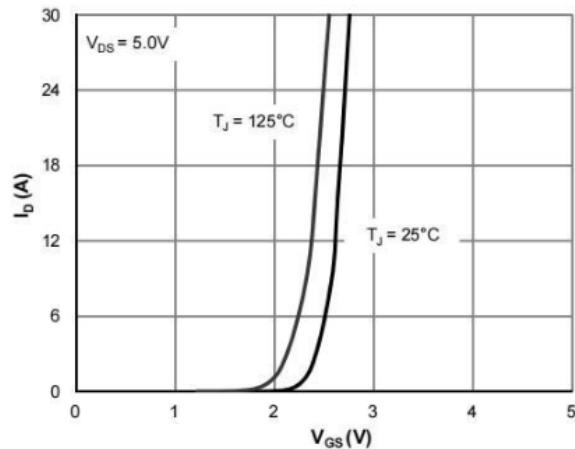
Notes:

1. E AS is tested at starting T_j = 25°C, V_{DD} = 50V, V_{GS} = 10V, L = 0.1mH, R_g = 25mΩ;

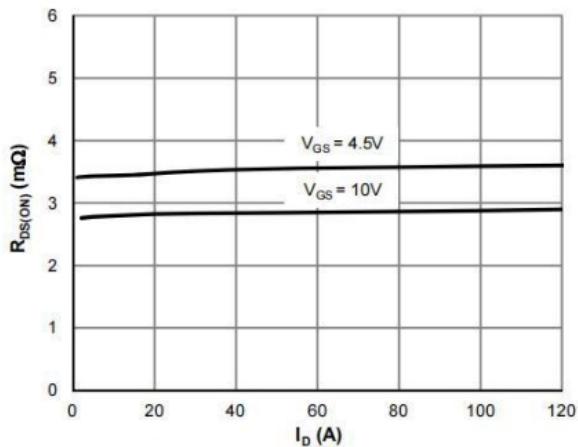
Typical Characteristics



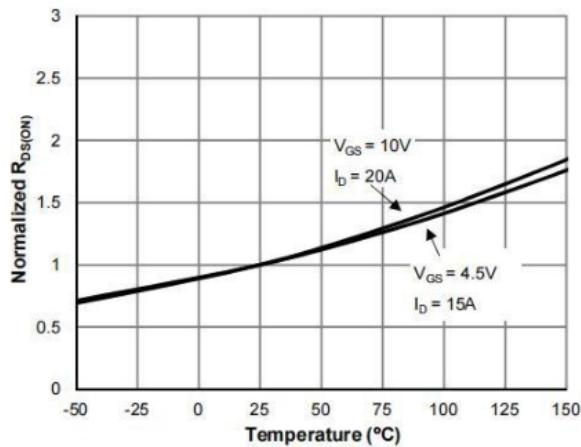
Typical Output Characteristics



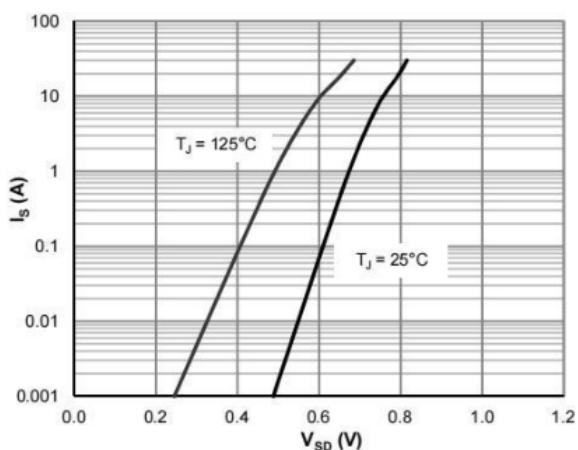
Transfer Characteristics



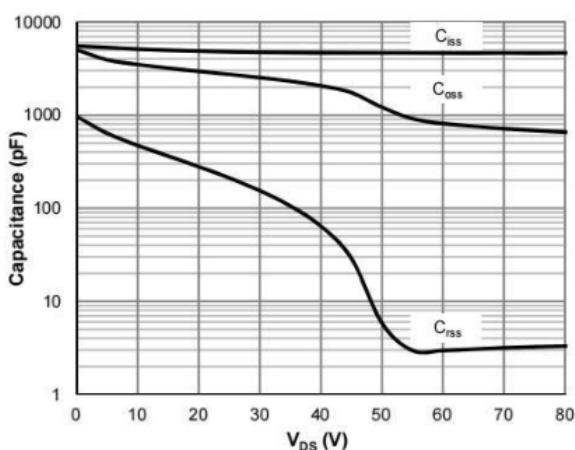
On-Resistance vs. Drain Current



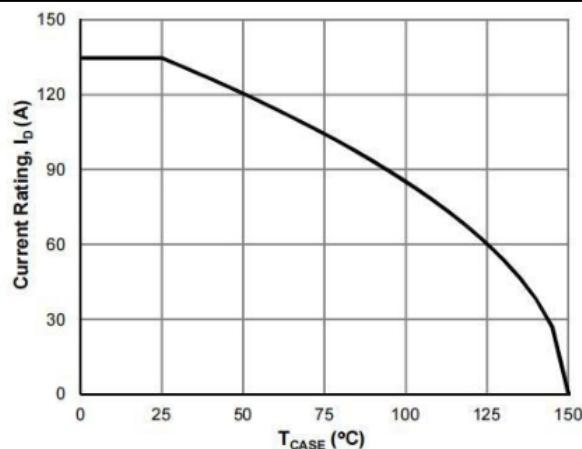
On-Resistance vs. Junction Temperature



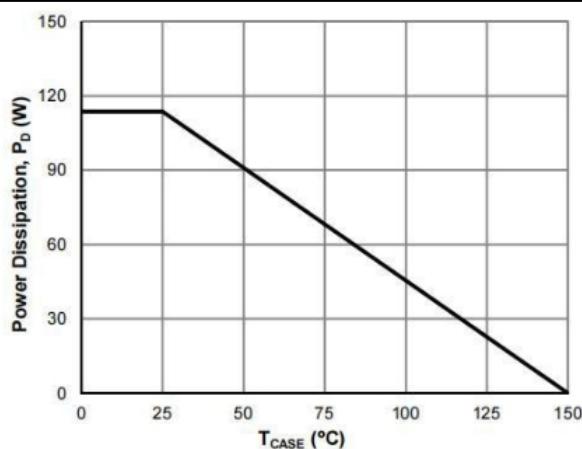
Body-Diode Characteristics



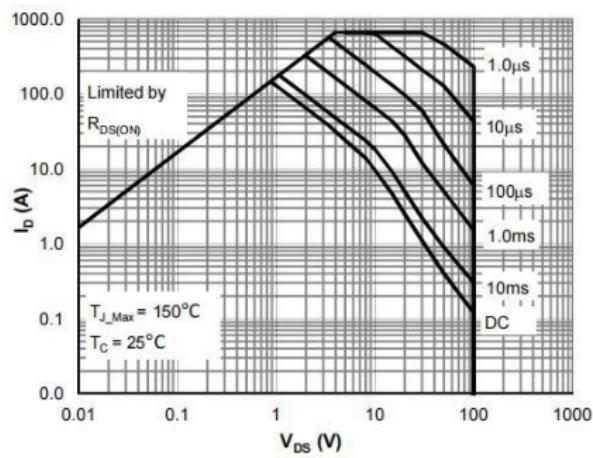
Capacitance Characteristics



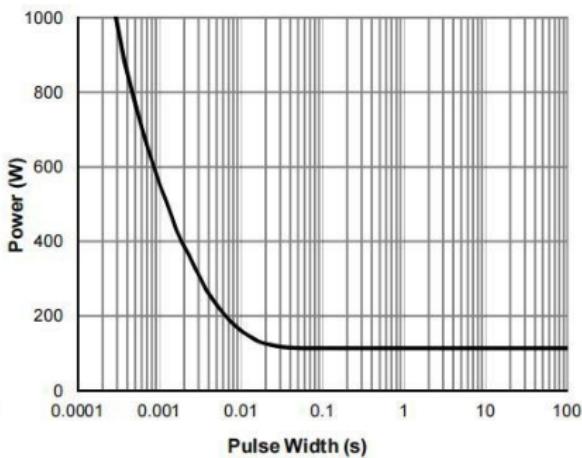
Current De-rating



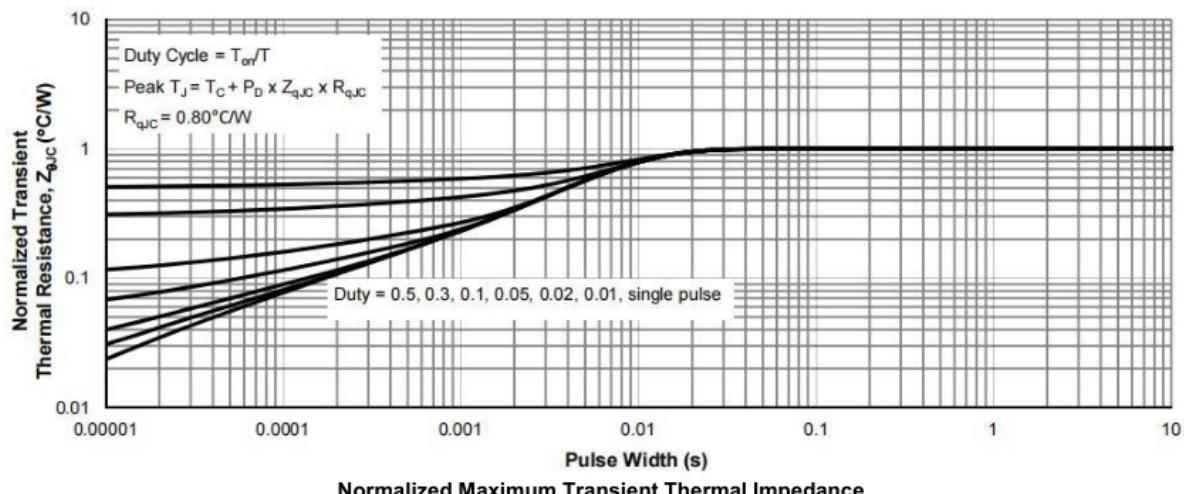
Power De-rating



Maximum Safe Operating Area

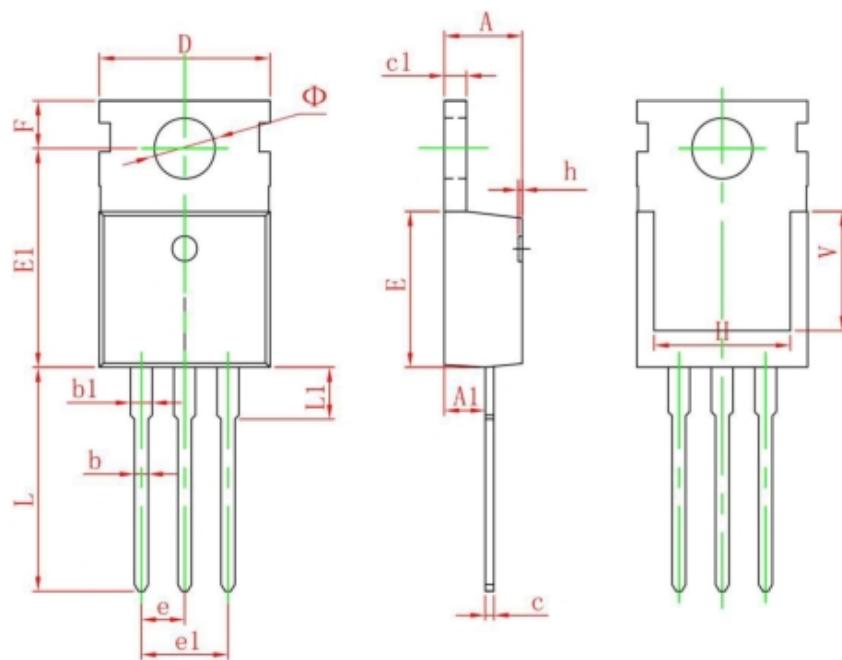


Single Pulse Power Rating, Junction-to-Case



Normalized Maximum Transient Thermal Impedance

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150